

SKKT 323; SKKH 323



SEMIPACK® 3

Thyristor / Diode Modules

SKKT 323

SKKH 323

Preliminary Data

Features

- Industrial standard package
- Electrically isolated base plate
- Heat transfer through aluminium oxide ceramic isolated metal base plate
- Chip soldered on direct copper bonded Al₂O₃ ceramic
- Thyristor chip with center gate
- UL recognition applied for file no. E63532

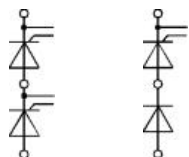
Typical Applications

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

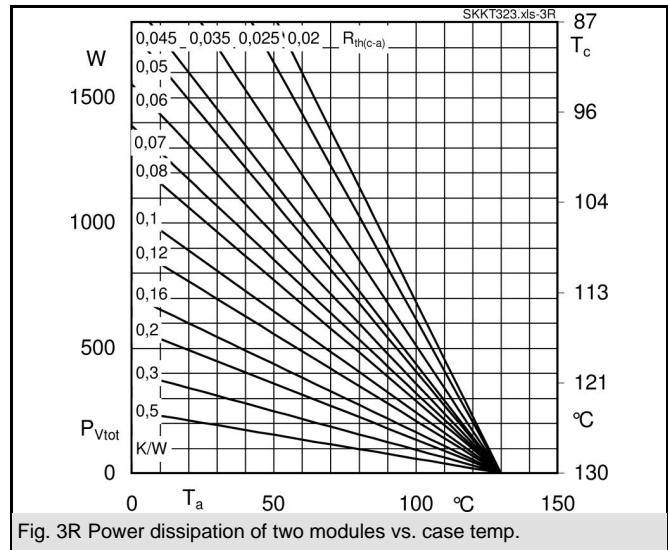
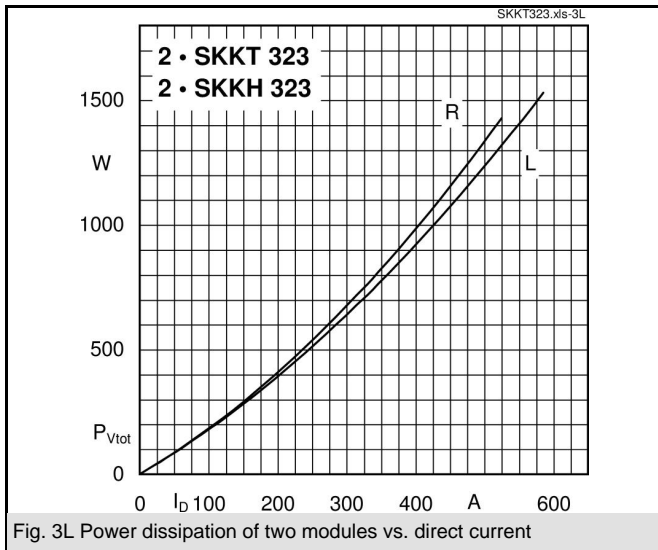
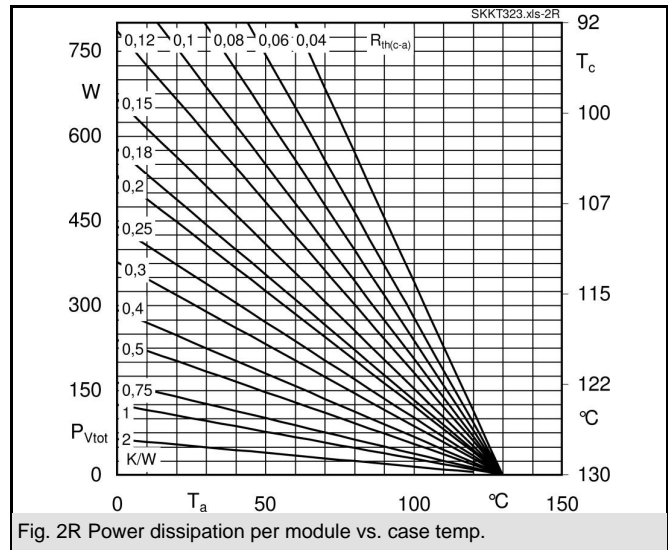
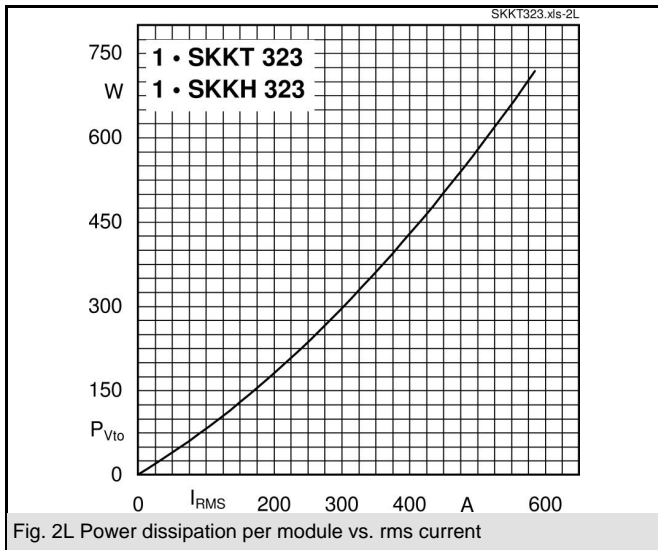
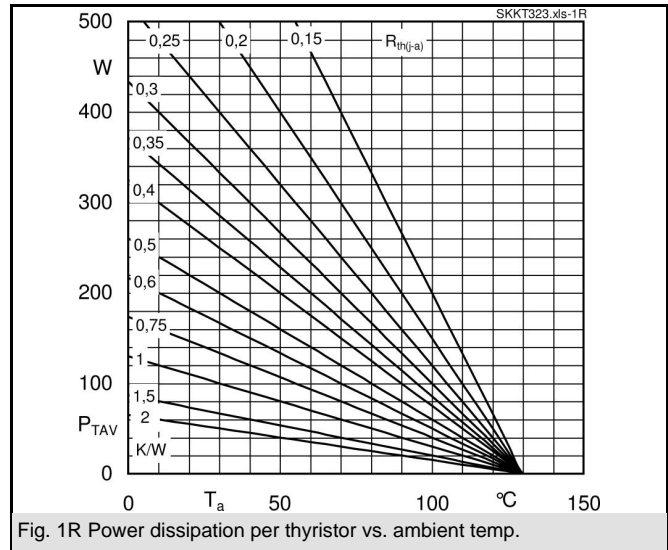
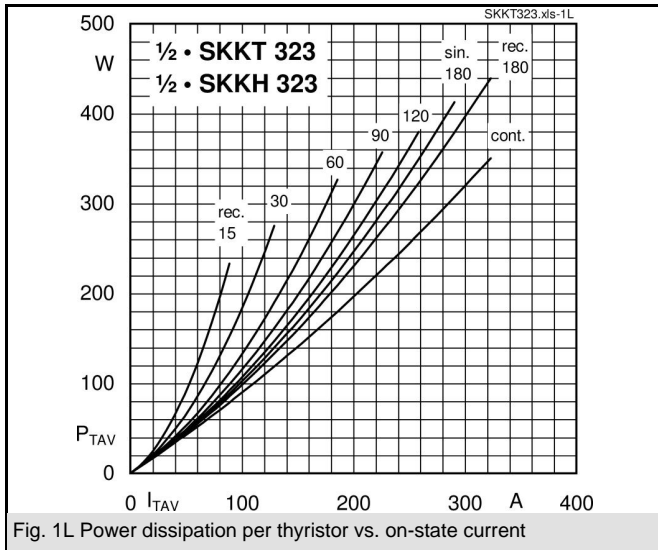
V_{RSM} V	$V_{RRM}; V_{DRM}$ V	$I_{TRMS} = 520$ A (maximum value for continuous operation)	
1300	1200	$I_{TAV} = 323$ A (sin. 180; $T_c = 84$ °C)	
1700	1600	SKKT 323/12E	SKKH 323/12E
		SKKT 323/16E	SKKH 323/16E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 85$ (100) °C;	320 (241)	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 130$ °C; 10 ms	9500 8200	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms $T_{vj} = 130$ °C; 8,3 ... 10 ms	450000 336000	A ² s
V_T	$T_{vj} = 25$ °C; $I_T = 750$ A	max. 1,45	V
$V_{T(TO)}$	$T_{vj} = 130$ °C	max. 0,81	V
r_T	$T_{vj} = 130$ °C	max. 0,85	mΩ
$I_{DD}; I_{RD}$	$T_{vj} = 130$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 100	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 130$ °C	max. 130	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 130$ °C	max. 1000	V/μs
t_q	$T_{vj} = 130$ °C, typ.	150	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	150 / 500	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 2000	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 2	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 150	mA
V_{GD}	$T_{vj} = 130$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 130$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,091 / 0,0455	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,095 / 0,0475	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,11 / 0,055	K/W
$R_{th(c-s)}$	per thyristor / per module	0,08 / 0,04	K/W
T_{vj}		- 40 ... + 130	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 % ¹⁾	Nm
M_t	to terminals	9 ± 15 %	Nm
a		5 * 9,81	m/s ²
m	approx.	410	g
Case	SKKT	A 43a	
	SKKH	A 56a	



SKKT

SKKH



SKKT 323; SKKH 323

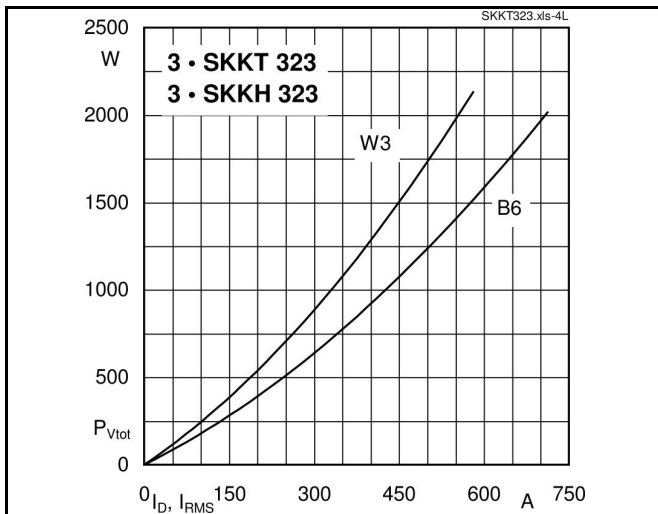


Fig. 4L Power dissipation of three modules vs. direct and rms current

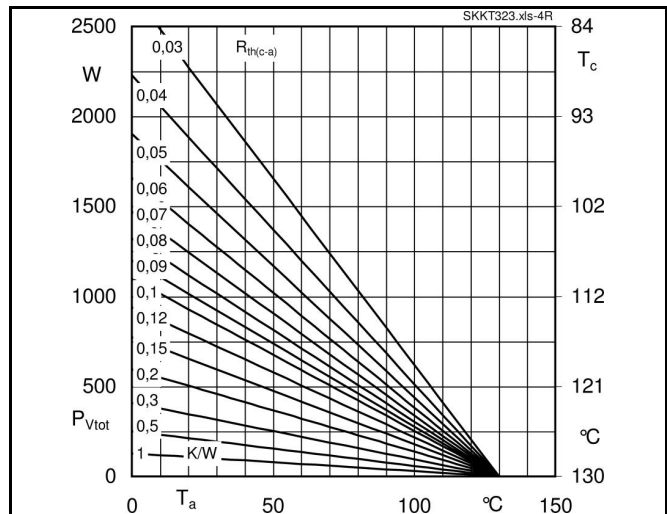


Fig. 4R Power dissipation of three modules vs. case temp.

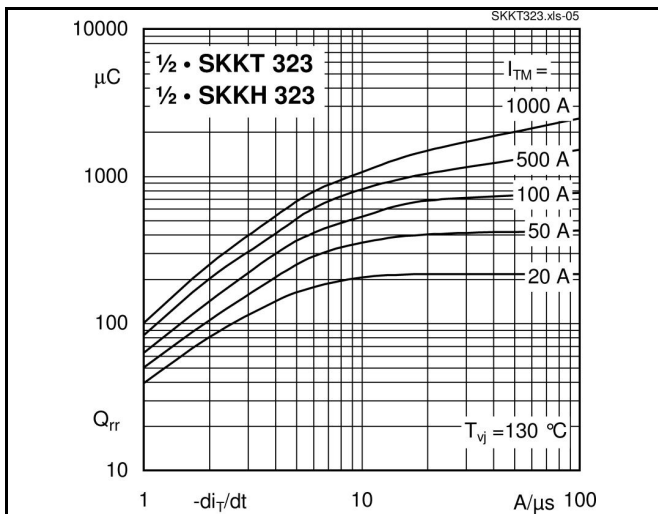


Fig. 5 Recovered charge vs. current decrease

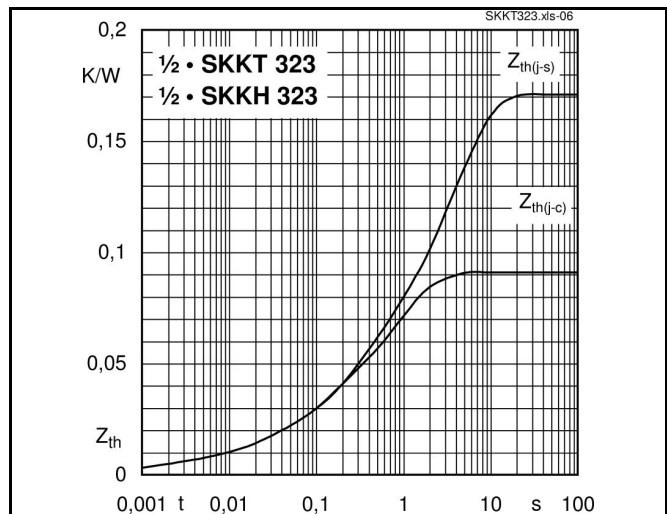


Fig. 6 Transient thermal impedance vs. time

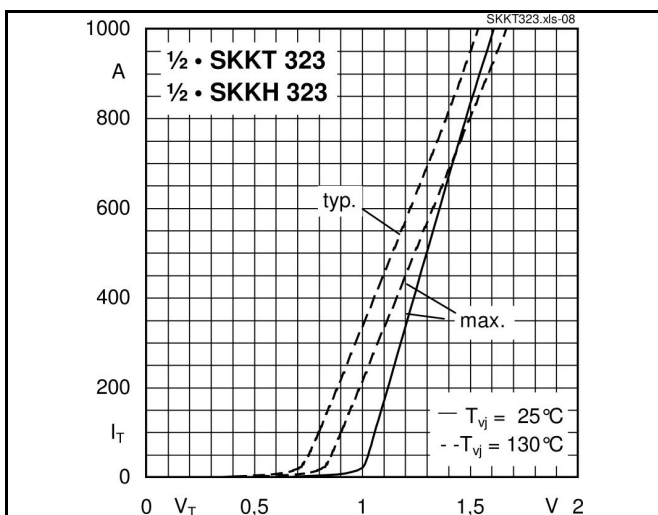


Fig. 7 On-state characteristics

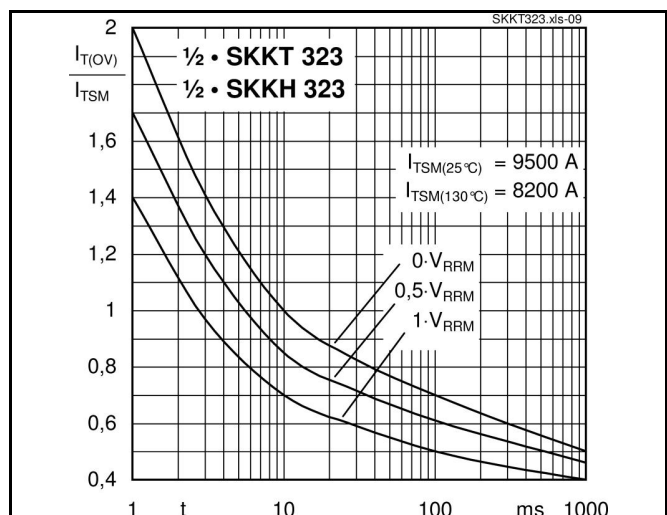
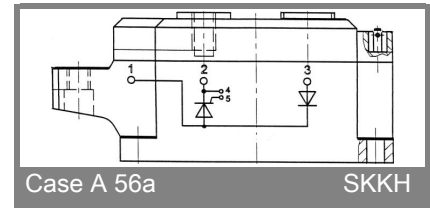
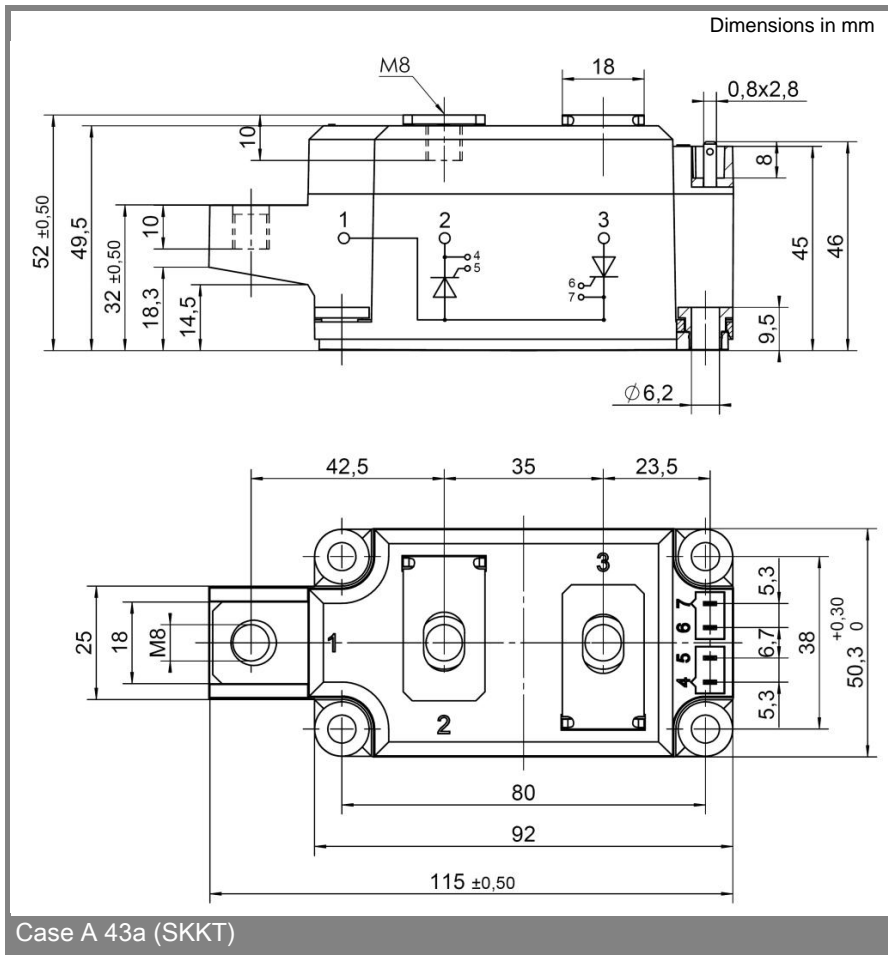
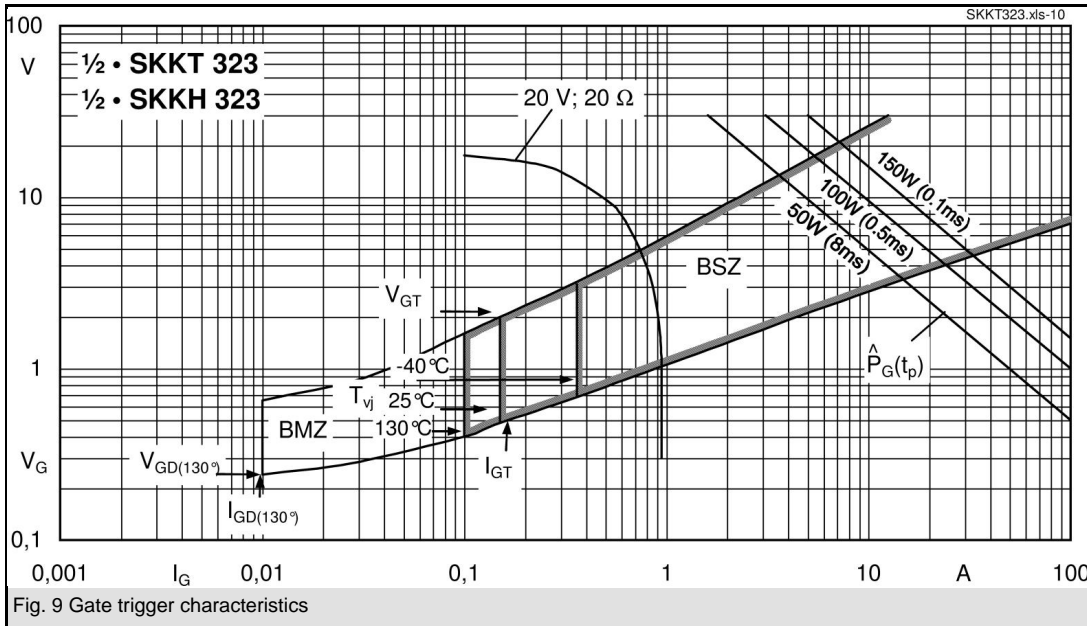


Fig. 8 Surge overload current vs. time



This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.